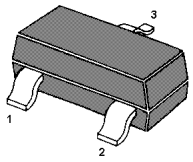
PNP Silicon Epitaxial Planar Transistor

for audio frequency, general purpose amplifier.

The transistor is subdivided into four groups O, Y, G and L, according to its DC current gain.



1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_S	-55 to +150	°C

Characteristics at T_{amb}=25 °C

		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain						
at $-V_{CE}$=6V, $-I_C$=1mA						
Current Gain Group	O	h_{FE}	90	-	180	-
	Y	h_{FE}	135	-	270	-
	G	h_{FE}	200	-	400	-
	L	h_{FE}	300	-	600	-
Collector Cutoff Current at $-V_{CB}$=60V		$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current at $-V_{EB}$=5V		$-I_{EBO}$	-	-	0.1	μA
Collector Saturation Voltage at $-I_C$=100mA, $-I_B$=10mA		$-V_{CE(sat)}$	-	-	0.3	V
Base Emitter Voltage at $-V_{CE}$=6V, $-I_C$=1mA		$-V_{BE}$	0.58	-	0.68	V
Gain Bandwidth Product at $-V_{CE}$=6V, $-I_C$=10mA		f_T	-	180	-	MHz
Output Capacitance at $-V_{CB}$=10V, f=1MHz		C_{OB}	-	4.5	-	pF